## Regulator with Enable, 150 mA, Low-Dropout Voltage, Low I<sub>q</sub>

The NCV4266-2C is a 150 mA output current integrated low dropout, low quiescent current regulator family designed for use in harsh automotive environments. It includes wide operating temperature and input voltage ranges. The device is offered with fixed voltage versions of 3.3 V and 5.0 V available in 2% output voltage accuracy. It has a high peak input voltage tolerance and reverse input voltage protection. It also provides overcurrent protection, overtemperature protection and enable function for control of the state of the output voltage. The NCV4266-2C is available in SOT-223 surface mount package. The output is stable over a wide output capacitance and ESR range. The NCV4266-2C has improved startup behavior during input voltage transients.

#### **Features**

- Output Voltage Options: 3.3 V, 5.0 V
- Output Voltage Accuracy: ±2.0%
- Output Current: up to 150 mA
- Low Quiescent Current (typ. 40 μA @ 100 μA)
- Low Dropout Voltage (typ. 250 mV @ 100 mA)
- Enable Input
- Fault Protection
  - +45 V Peak Transient Voltage
  - → -42 V Reverse Voltage
  - Short Circuit
  - Thermal Overload
- NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These are Pb-Free Devices

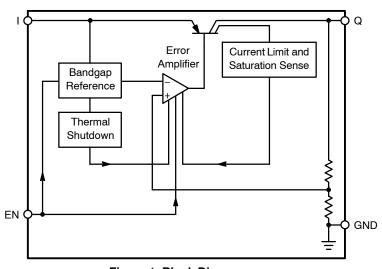


Figure 1. Block Diagram



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SOT-223 ST SUFFIX CASE 318E

#### **MARKING DIAGRAM**



A = Assembly Location

Y = Year

W = Work Week

x = Voltage Option

3.3 V (x = 3)

5.0 V (x = 5) = Pb-Free Package

(Note: Microdot may be in either location)

#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the ordering information section on page 10 of this data sheet.

#### PIN FUNCTION DESCRIPTION

Pin No.	Pin No.		
DFN8		Symbol	Description
1	1	I	Input; Battery Supply Input Voltage.
3	2	EN	Enable Input; Low level disables the IC.
4	3	Q	Output; Bypass with a capacitor to GND.
8	4	GND	Ground.

## **MAXIMUM RATINGS**

Rating		Symbol	Min	Max	Unit
Input Voltage		VI	-42	45	V
Input Peak Transient Voltage		VI	-	45	V
Enable Input Voltage		V <sub>EN</sub>	-42	45	V
Output Voltage		V <sub>Q</sub>	-0.3	32	V
Ground Current		Ιq	-	100	mA
Input Voltage Operating Range		V <sub>I</sub>	V <sub>Q</sub> + 0.5 V or 4.5 (Note 1)	45	<b>V</b>
ESD Susceptibility	(Human Body Model)	-	3.0	-	kV
Junction Temperature		TJ	-40	150	°C
Storage Temperature		T <sub>stg</sub>	-50	150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

## LEAD TEMPERATURE SOLDERING REFLOW AND MSL (Note 2)

Rating	Symbol	Min	Max	Unit
Lead Temperature Soldering Reflow (SMD styles only), Leaded, 60–150 s above 183, 30 s max at peak Reflow (SMD styles only), Free, 60–150 s above 217, 40 s max at peak Wave Solder (through hole styles only), 12 sec max	T <sub>SLD</sub>	- - -	240 265 310	°C
Moisture Sensitivity Level	MSL	3	3	_

<sup>2.</sup> Per IPC / JEDEC J-STD-020C.

#### THERMAL RESISTANCE

Parameter		Symbol	Condition	Min	Max	Unit
Junction-to-Ambient	SOT-223	$R_{ hetaJA}$		-	109 (Note 3)	°C/W
Junction-to-Tab	SOT-223	Rψ <sub>JT</sub>		-	10.9	°C/W

<sup>3. 1</sup> oz copper, 100 mm² copper area, FR4.

<sup>1.</sup> Minimum  $V_I = 4.5 \text{ V or } (V_Q + 0.5 \text{ V})$ , whichever is higher.

 $\textbf{ELECTRICAL CHARACTERISTICS} \quad (-40^{\circ}C < T_{J} < 150^{\circ}C, \ V_{I} = 13.5 \ V, \ V_{EN} = 5 \ V; \ unless otherwise noted.)$ 

Characteristic	Symbol	Test Conditions	Min	Тур	Max	Unit
OUTPUT					•	
Output Voltage (5.0 V Version)	VQ	$100~\mu\text{A} < I_Q < 150~\text{mA},~6.0~\text{V} < V_I < 28~\text{V}$	4.9	5.0	5.1	V
Output Voltage (3.3 V Version)	VQ	$100~\mu\text{A} < \text{I}_{\text{Q}} < 150~\text{mA},~4.5~\text{V} < \text{V}_{\text{I}} < 28~\text{V}$	3.234	3.3	3.366	V
Output Current Limitation	IQ	V <sub>Q</sub> = 90% V <sub>QTYP</sub>	150	390	500	mA
Quiescent Current (Sleep Mode) I <sub>q</sub> = I <sub>I</sub> - I <sub>Q</sub>	Iq	$V_{EN} = 0 \text{ V}, T_J = -40^{\circ}\text{C} \text{ to } 100^{\circ}\text{C}$	-	0	1.0	μΑ
Quiescent Current, I <sub>q</sub> = I <sub>I</sub> - I <sub>Q</sub>	Iq	I <sub>Q</sub> = 100 μA, T <sub>J</sub> < 85°C	_	40	60	μΑ
Quiescent Current, I <sub>q</sub> = I <sub>I</sub> - I <sub>Q</sub>	Iq	$I_Q = 100 \mu A$	_	40	70	μΑ
Quiescent Current, I <sub>q</sub> = I <sub>I</sub> - I <sub>Q</sub>	Iq	I <sub>Q</sub> = 50 mA	_	0.55	4.0	mA
Dropout Voltage (5.0 V Version)	$V_{DR}$	$I_Q = 100 \text{ mA}, V_{DR} = V_I - V_Q \text{ (Note 4)}$	-	230	500	mV
Load Regulation (5.0 V Version)	$\Delta V_{Q,LO}$	I <sub>Q</sub> = 1.0 mA to 100 mA	-	3.5	90	mV
Load Regulation (3.3 V Version)	$\Delta V_{Q,LO}$	I <sub>Q</sub> = 1.0 mA to 100 mA	-	0.5	60	mV
Line Regulation (5.0 V Version)	$\Delta V_{Q}$	$\Delta V_{I}$ = 6.0 V to 28 V, $I_{Q}$ = 1.0 mA	-	1.0	30	mV
Line Regulation (3.3 V Version)	$\Delta V_{Q}$	$\Delta V_{I}$ = 4.5 V to 28 V, $I_{Q}$ = 1.0 mA	-	0.5	20	mV
Power Supply Ripple Rejection	PSRR	$f_r = 100 \text{ Hz}, V_r = 0.5 \text{ V}_{PP}$	-	68	-	dB
ENABLE INPUT						
Enable Voltage, Output High	V <sub>EN</sub>	$V_Q \ge V_{QMIN}$	-	2.0	2.7	V
Enable Voltage, Output Low (Off)	V <sub>EN</sub>	$V_Q \leq 0.1 \text{ V}$	0.8	1.8	-	V
Enable Input Current	I <sub>EN</sub>	V <sub>EN</sub> = 5.0 V	-	4.0	8.0	μΑ
THERMAL SHUTDOWN	•		•		•	
Thermal Shutdown Temperature*	T <sub>SD</sub>		150	-	200	°C

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

<sup>4.</sup> Measured when the output voltage  $V_Q$  has dropped 100 mV from the nominal value obtained at V = 13.5 V.

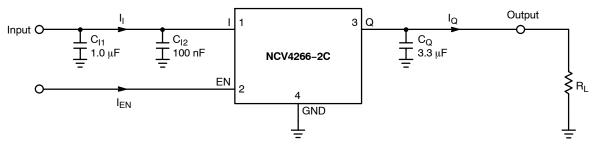


Figure 2. Applications Circuit

<sup>\*</sup>Guaranteed by design, not tested in production.

## TYPICAL CHARACTERISTICS CURVES - 5 V Version

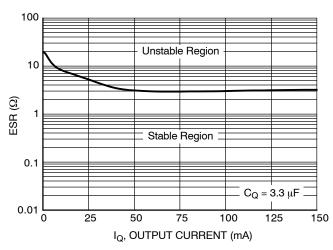
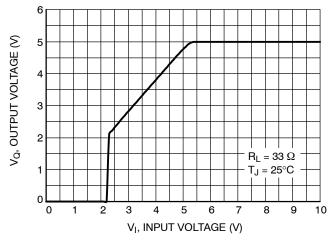


Figure 3. Output Stability with Output Capacitor ESR

Figure 4. Output Voltage vs. Junction Temperature



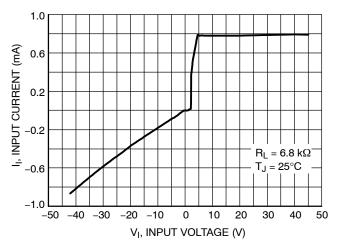
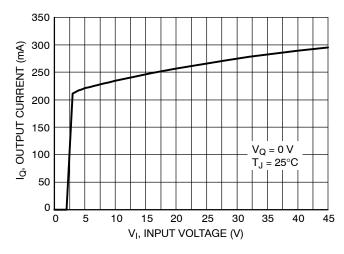


Figure 5. Output Voltage vs. Input Voltage

Figure 6. Input Current vs. Input Voltage



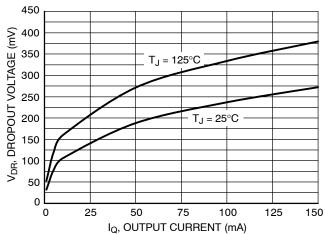
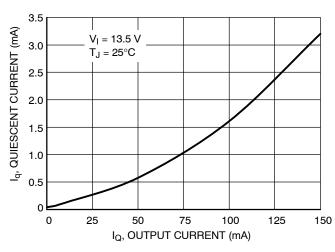


Figure 7. Maximum Output Current vs. Input Voltage

Figure 8. Dropout Voltage vs. Output Current

## TYPICAL CHARACTERISTICS CURVES - 5 V Version



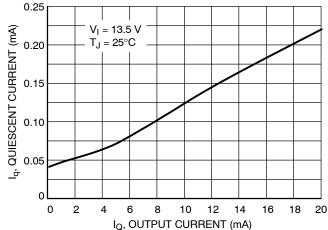


Figure 9. Quiescent Current vs. Output Current (High Load)

Figure 10. Quiescent Current vs. Output Current (Low Load)

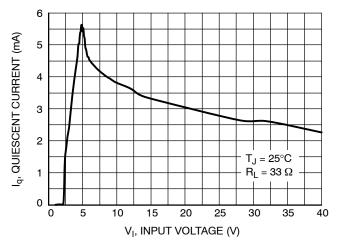
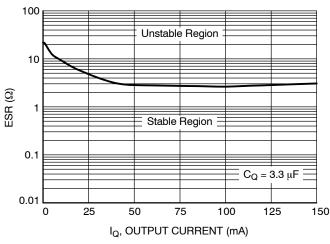


Figure 11. Quiescent Current vs. Input Voltage

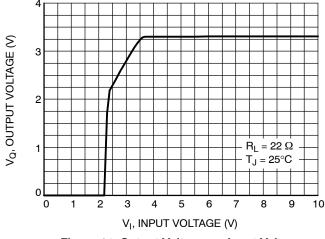
#### TYPICAL CHARACTERISTICS CURVES - 3.3 V Version



3.36 (S) 3.34 3.32 3.32 3.38 3.28 3.24 -40 0 40 80 120 160 T<sub>J</sub>, JUNCTION TEMPERATURE (°C)

Figure 12. Output Stability with Output Capacitor ESR

Figure 13. Output Voltage vs. Junction Temperature



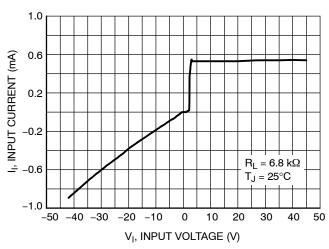
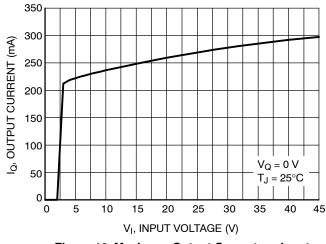


Figure 14. Output Voltage vs. Input Voltage

Figure 15. Input Current vs. Input Voltage



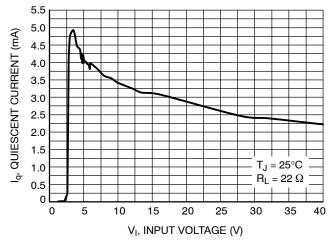
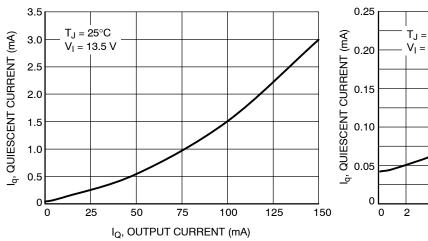


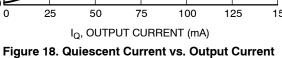
Figure 16. Maximum Output Current vs. Input Voltage

Figure 17. Quiescent Current vs. Input Voltage

## **TYPICAL CHARACTERISTICS CURVES - 3.3 V Version**



(High Load)



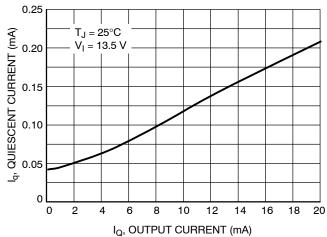


Figure 19. Quiescent Current vs. Output Current (Low Load)

#### **Circuit Description**

The NCV4266–2C is an integrated low dropout regulator that provides a regulated voltage at 150 mA to the output. It is enabled with an input to the enable pin. The regulator voltage is provided by a PNP pass transistor controlled by an error amplifier with a bandgap reference, which gives it the lowest possible dropout voltage. The output current capability is 150 mA, and the base drive quiescent current is controlled to prevent oversaturation when the input voltage is low or when the output is overloaded. The regulator is protected by both current limit and thermal shutdown. Thermal shutdown occurs above 150°C to protect the IC during overloads and extreme ambient temperatures.

#### Regulator

The error amplifier compares the reference voltage to a sample of the output voltage  $(V_Q)$  and drives the base of a PNP series pass transistor via a buffer. The reference is a bandgap design to give it a temperature–stable output. Saturation control of the PNP is a function of the load current and input voltage. Oversaturation of the output power device is prevented, and quiescent current in the ground pin is minimized. See Figure 2, Test Circuit, for circuit element nomenclature illustration.

## **Regulator Stability Considerations**

The input capacitors ( $C_{I1}$  and  $C_{I2}$ ) are necessary to stabilize the input impedance to avoid voltage line influences. Using a resistor of approximately 1.0  $\Omega$  in series with  $C_{I2}$  can stop potential oscillations caused by stray inductance and capacitance.

The output capacitor helps determine three main characteristics of a linear regulator: startup delay, load

transient response and loop stability. The capacitor value and type should be based on cost, availability, size and temperature constraints. The aluminum electrolytic capacitor is the least expensive solution, but, if the circuit operates at low temperatures (-25°C to -40°C), both the value and ESR of the capacitor will vary considerably. The capacitor manufacturer's data sheet usually provides this information.

The value for the output capacitor  $C_Q$ , shown in Figure 2, should work for most applications; see also Figures 3 and 12 for output stability at various load and Output Capacitor ESR conditions. Stable region of ESR in Figures 3 and 12 shows ESR values at which the LDO output voltage does not have any permanent oscillations at any dynamic changes of output load current. Marginal ESR is the value at which the output voltage waving is fully damped during five periods after the load change and no oscillation is further observable.

ESR characteristics were measured with ceramic capacitors and additional series resistors to emulate ESR. Low duty cycle pulse load current technique has been used to maintain junction temperature close to ambient temperature.

#### **Enable Input**

The enable pin is used to turn the regulator on or off. By holding the pin down to a voltage less than 0.8 V, the output of the regulator will be turned off. When the voltage on the enable pin is greater than 2.7 V, the output of the regulator will be enabled to power its output to the regulated output voltage. The enable pin may be connected directly to the input pin to give constant enable to the output regulator.

# Calculating Power Dissipation in a Single Output Linear Regulator

The maximum power dissipation for a single output regulator (Figure 20) is:

$$PD(max) = [VI(max) - VQ(min)] IQ(max) + VI(max)Iq$$
(eq. 1)

where

 $\begin{array}{ll} V_{I(max)} & \text{is the maximum input voltage,} \\ V_{Q(min)} & \text{is the minimum output voltage,} \end{array}$ 

 $I_{Q(max)}$  is the maximum output current for the

application,

 $I_{q}$  is the quiescent current the regulator

consumes at I<sub>Q(max)</sub>.

Once the value of  $P_{D(max)}$  is known, the maximum permissible value of  $R_{\theta JA}$  can be calculated:

$$R_{\theta JA} = \frac{150^{0}C - T_{A}}{P_{D}} \tag{eq. 2} \label{eq:power}$$

The value of  $R_{\theta JA}$  can then be compared with those in the package section of the data sheet. Those packages with  $R_{\theta JA}$  less than the calculated value in Equation 2 will keep the die temperature below 150°C.

In some cases, none of the packages will be sufficient to dissipate the heat generated by the IC, and an external heatsink will be required.

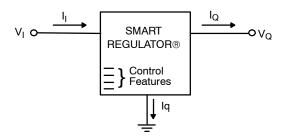


Figure 20. Single Output Regulator with Key Performance Parameters Labeled

#### **Heatsinks**

A heatsink effectively increases the surface area of the package to improve the flow of heat away from the IC and into the surrounding air.

Each material in the heat flow path between the IC and the outside environment will have a thermal resistance. Like series electrical resistances, these resistances are summed to determine the value of  $R_{\theta JA}$ :

$$R_{\theta}JA = R_{\theta}JC + R_{\theta}CS + R_{\theta}SA$$
 (eq. 3)

where

 $\begin{array}{ll} R_{\theta JC} & \text{is the junction-to-case thermal resistance,} \\ R_{\theta CS} & \text{is the case-to-heatsink thermal resistance,} \\ R_{\theta SA} & \text{is the heatsink-to-ambient thermal} \end{array}$ 

resistance.

 $R_{\theta JC}$  appears in the package section of the data sheet. Like  $R_{\theta JA}$ , it too is a function of package type.  $R_{\theta CS}$  and  $R_{\theta SA}$  are functions of the package type, heatsink and the interface between them. These values appear in data sheets of heatsink manufacturers.

Thermal, mounting, and heatsinking considerations are discussed in the ON Semiconductor application note AN1040/D.

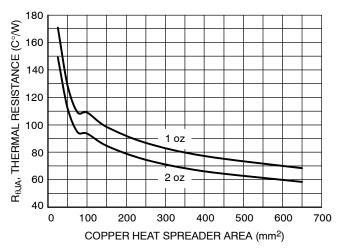


Figure 21.  $R_{\theta JA}$  vs. Copper Spreader Area, SOT–223

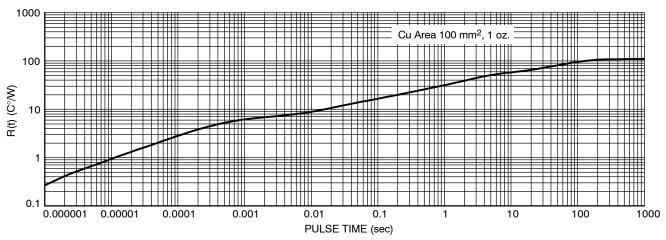


Figure 22. Single-Pulse Heating Curve, SOT-223

## **ORDERING INFORMATION**

Device*	Output Voltage	Package	Shipping <sup>†</sup>
NCV4266-2CST33T3G	3.3 V	SOT-223 (Pb-Free)	4000 / Tape & Reel
NCV4266-2CST50T3G	5.0 V	SOT-223 (Pb-Free)	4000 / Tape & Reel

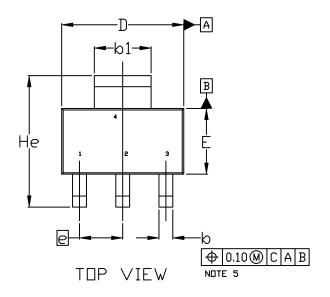
<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

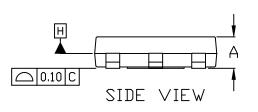
<sup>\*</sup>NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

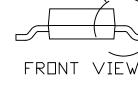


**SOT-223 (TO-261)** CASE 318E-04 ISSUE R

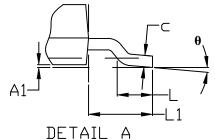
**DATE 02 OCT 2018** 







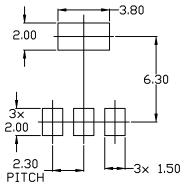
SEE DETAIL A



#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. DIMENSIONS D & E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
  MOLD FLASH, PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.200MM PER SIDE.
- 4. DATUMS A AND B ARE DETERMINED AT DATUM H.
- 5. ALLIS DEFINED AS THE VERTICAL DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT OF THE PACKAGE BODY.
- 6. POSITIONAL TOLERANCE APPLIES TO DIMENSIONS 6 AND 61.

	MILLIMETERS				
DIM	MIN.	N□M.	MAX.		
Α	1.50	1.63	1.75		
A1	0.02	0.06	0.10		
b	0.60	0.75	0.89		
b1	2.90	3.06	3.20		
C	0.24	0.29	0.35		
D	6.30	6.50	6.70		
E	3.30	3.50	3.70		
е		2,30 BSC	,		
L	0.20				
L1	1.50	1.75	2.00		
He	6.70	7.00	7.30		
θ	0°		10°		



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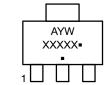
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## **SOT-223 (TO-261)** CASE 318E-04 ISSUE R

**DATE 02 OCT 2018** 

STYLE 1: PIN 1. BASE 2. COLLECTOR 3. EMITTER 4. COLLECTOR	STYLE 2: PIN 1. ANODE 2. CATHODE 3. NC 4. CATHODE	STYLE 3: PIN 1. GATE 2. DRAIN 3. SOURCE 4. DRAIN	STYLE 4: PIN 1. SOURCE 2. DRAIN 3. GATE 4. DRAIN	STYLE 5: PIN 1. DRAIN 2. GATE 3. SOURCE 4. GATE
STYLE 6: PIN 1. RETURN 2. INPUT 3. OUTPUT 4. INPUT	STYLE 7: PIN 1. ANODE 1 2. CATHODE 3. ANODE 2 4. CATHODE	4. DHAIN STYLE 8: CANCELLED	STYLE 9: PIN 1. INPUT 2. GROUND 3. LOGIC 4. GROUND	STYLE 10: PIN 1. CATHODE 2. ANODE 3. GATE 4. ANODE
STYLE 11: PIN 1. MT 1 2. MT 2 3. GATE 4. MT 2	STYLE 12: PIN 1. INPUT 2. OUTPUT 3. NC 4. OUTPUT	STYLE 13: PIN 1. GATE 2. COLLECTOR 3. EMITTER 4. COLLECTOR		

## GENERIC MARKING DIAGRAM\*



A = Assembly Location

Y = Year W = Work Week

XXXXX = Specific Device Code

= Pb-Free Package

(Note: Microdot may be in either location)
\*This information is generic. Please refer to
device data sheet for actual part marking.
Pb-Free indicator, "G" or microdot "•", may
or may not be present. Some products may
not follow the Generic Marking.

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